

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S17 | 1721 | 257/355.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 02:46 |
| S18 | 675 | 257/356.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 04:05 |
| S19 | 865 | 257/360.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 04:31 |
| S20 | 410 | 257/346.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 14:58 |
| S21 | 82 | semiconductor and (ESD or protection or overvoltage) and (triple near2 well) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:02 |
| S22 | 5647 | semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:03 |
| S23 | 1402 | semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:15 |
| S24 | 1241 | semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (source or drain or cmos or mosfet or fet) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:04 |

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|-----|------|--|---|----|----|------------------|
| S25 | 397 | semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (source or drain or cmos or mosfet or fet) and (substrate with resistance) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:05 |
| S26 | 442 | semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (substrate with resistance) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:15 |
| S27 | 417 | semiconductor and (ESD or protection or overvoltage) and (wells same (substrate near4 contact)) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 05:15 |
| S28 | 570 | 257/E27.067.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 15:23 |
| S29 | 308 | 257/E29.064.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 15:41 |
| S30 | 2990 | 257/E29.255.ccls. and (@ad<"20040408" or @rlad<"20040408") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 15:42 |
| S31 | 413 | 257/E29.255.ccls. and (@ad<"20040408" or @rlad<"20040408") and (substrate with contact) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/13 15:42 |